Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Supporting Information for

Non-invasively improving the Schottky barrier of MoS_2/metal contacts by inserting SiC layer

Qinglong Fang,[a, b] Xumei Zhao,[a] Lin Yuan,[a] Boyu Wang,[a] Caijuan Xia,[a, *] Fei Ma[b, *]

[a] *School of Science, Xi'an Polytechnic University, Xi'an, 710048, Shaanxi, China*

[b] *State Key Laboratory for Mechanical Behavior of Materials, Xi'an Jiaotong University, Xi'an 710049, Shaanxi, China*

* Corresponding authors.

E−mail addresses: mafei@mail.xjtu.edu.cn (Fei Ma); caijuanxia@xpu.edu.cn (Caijuan Xia).

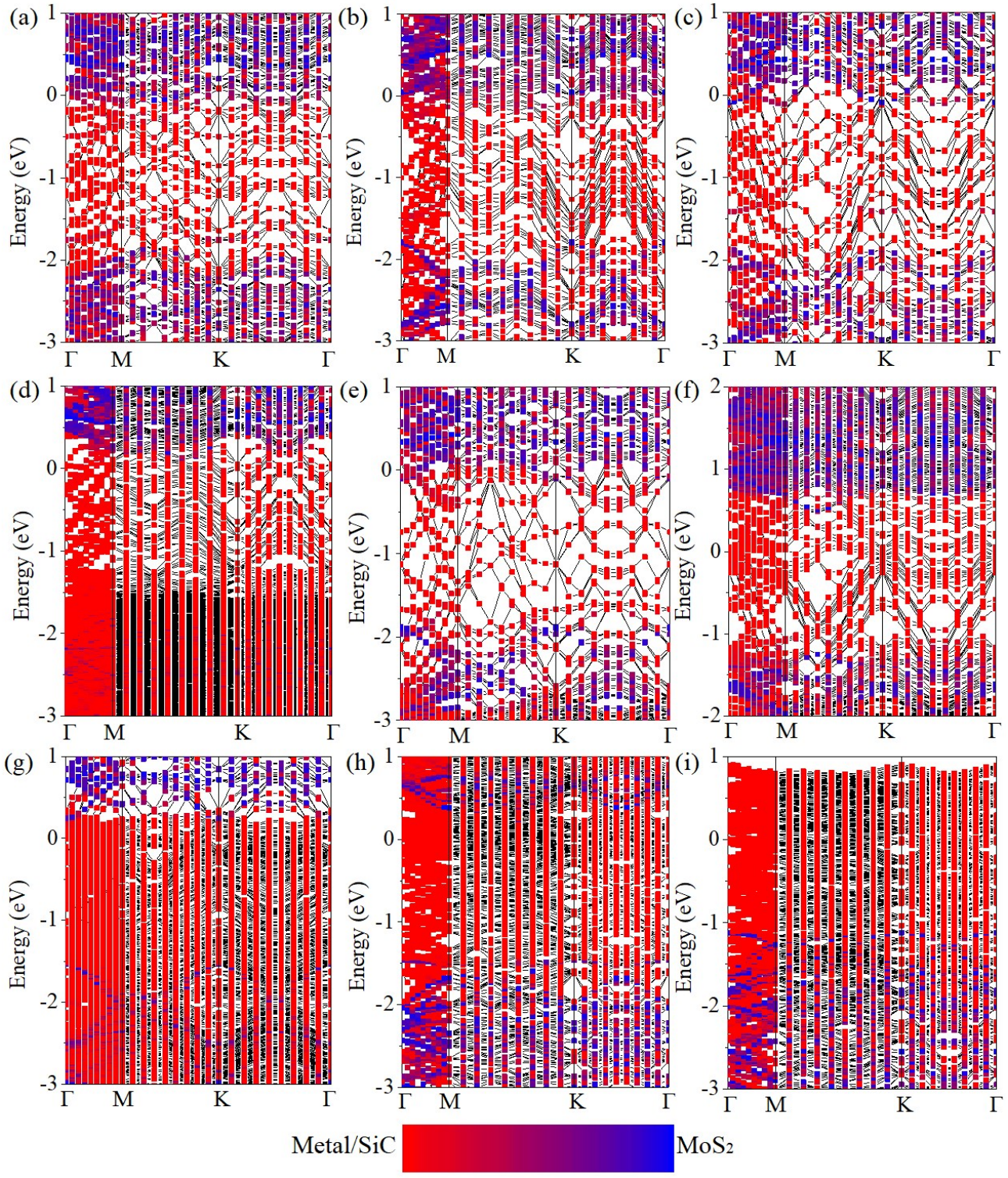

Figure S1. Band structures of the MoS_2/metals by inserting SiC layer: (a) Mg, (b) Al, (c) In, (d) Cu, (e) Ag, (f) Au, (g) Pd, (h) Sc, and (i) Ti.

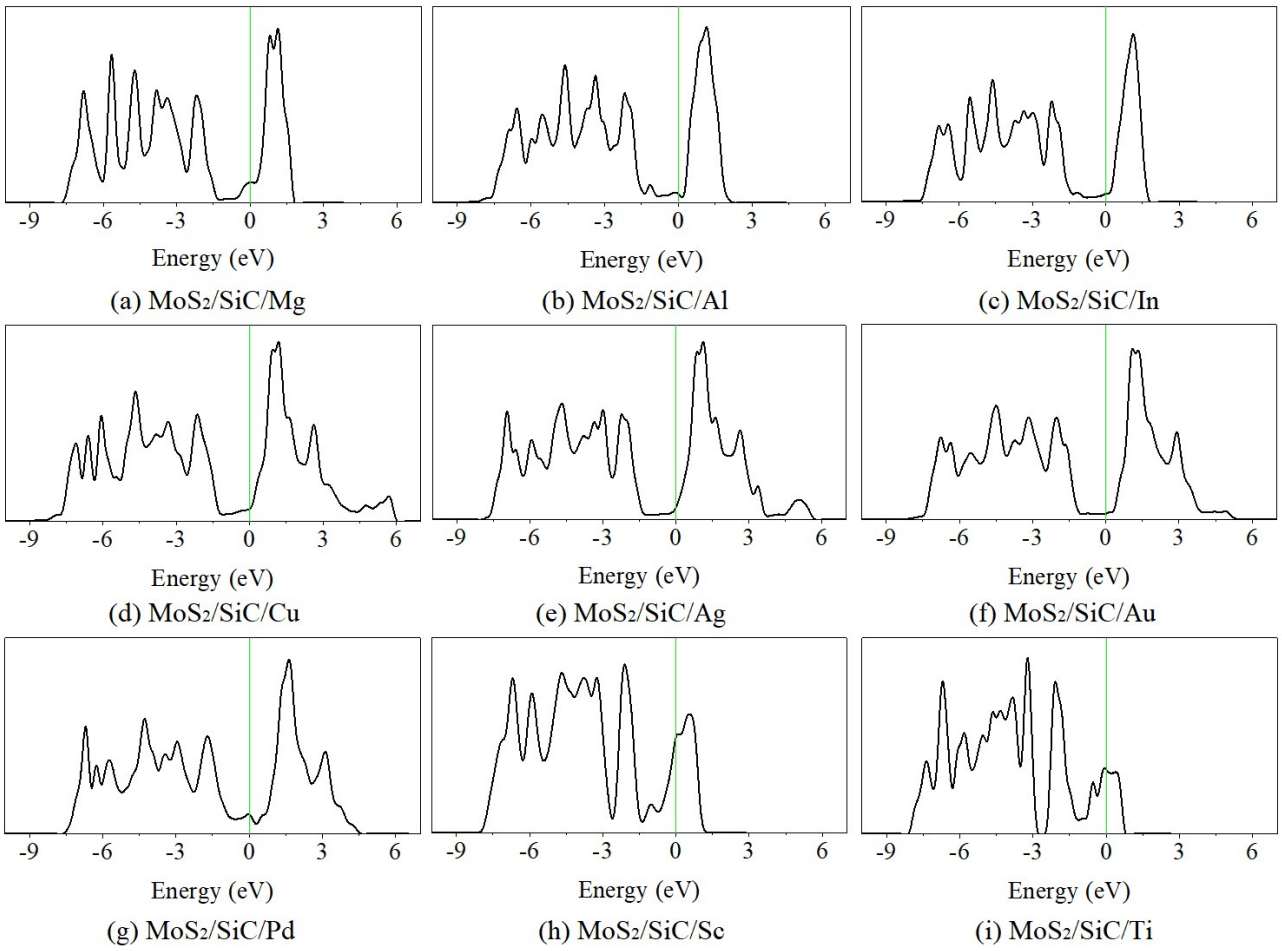

Figure S2. Partial density of states (PDOS) of monolayer MoS_2 in MoS_2/metals by inserting SiC layer.

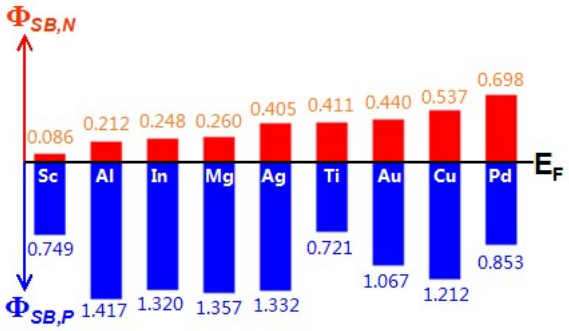

Fig. S3. Schottky barrier height (Φ_{SB}) of MoS_2/metals.